

SANYO

No.3455

2SK1452

N-Channel MOS Silicon FET

Very High-Speed Switching Applications

Features

- Low ON-state resistance.
- Very high-speed switching.
- Converters.
- Micaless package facilitating mounting.

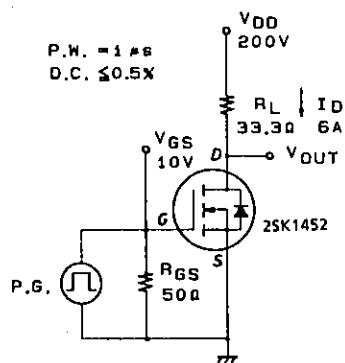
Absolute Maximum Ratings at Ta = 25°C

			unit
Drain to Source Voltage	V _{DSS}	450	V
Gate to Source Voltage	V _{GSS}	±30	V
Drain Current(DC)	I _D	10	A
Drain Current(Pulse)	I _{DP}	PW≤10μs, duty cycle≤1%	40 A
Allowable Power Dissipation	P _D	T _c =25°C	60 W
			3.0 W
Channel Temperature	T _{ch}	150	°C
Storage Temperature	T _{stg}	-55 to +150	°C

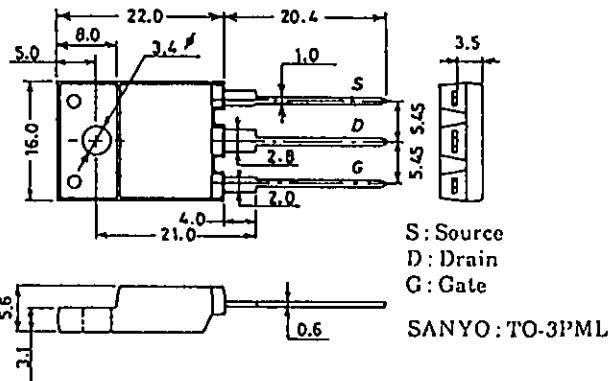
Electrical Characteristics at Ta = 25°C

			min	typ	max	unit
D-S Breakdown Voltage	V _{(BR)DSS}	I _D =1mA, V _{GS} =0	450			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =450V, V _{GS} =0			1.0	mA
Gate to Source Leakage Current	I _{GSS}	V _{GS} =±30V, V _{DS} =0			±100	nA
Cutoff Voltage	V _{GS(off)}	V _{DS} =10V, I _D =1mA	2.0		3.0	V
Forward Transfer Admittance	Y _{fs}	V _{DS} =10V, I _D =6A	4.0	8.0		S
Static Drain to Source on State Resistance	R _{DS(on)}	I _D =6A, V _{GS} =10V		0.47	0.6	Ω
Input Capacitance	C _{iss}	V _{DS} =20V, f=1MHz	1600			pF
Output Capacitance	C _{oss}	V _{DS} =20V, f=1MHz	220			pF
Reverse Transfer Capacitance	C _{rss}	V _{DS} =20V, f=1MHz	80			pF
Turn-ON Delay Time	t _{d(on)}			25		ns
Rise Time	t _r	I _D =6A, V _{GS} =10V		60		ns
Turn-OFF Delay Time	t _{d(off)}	V _{DD} =200V, R _{GS} =50Ω		250		ns
Fall Time	t _f			80		ns
Diode Forward Voltage	V _{SD}	I _S =10A, V _{GS} =0			1.8	V

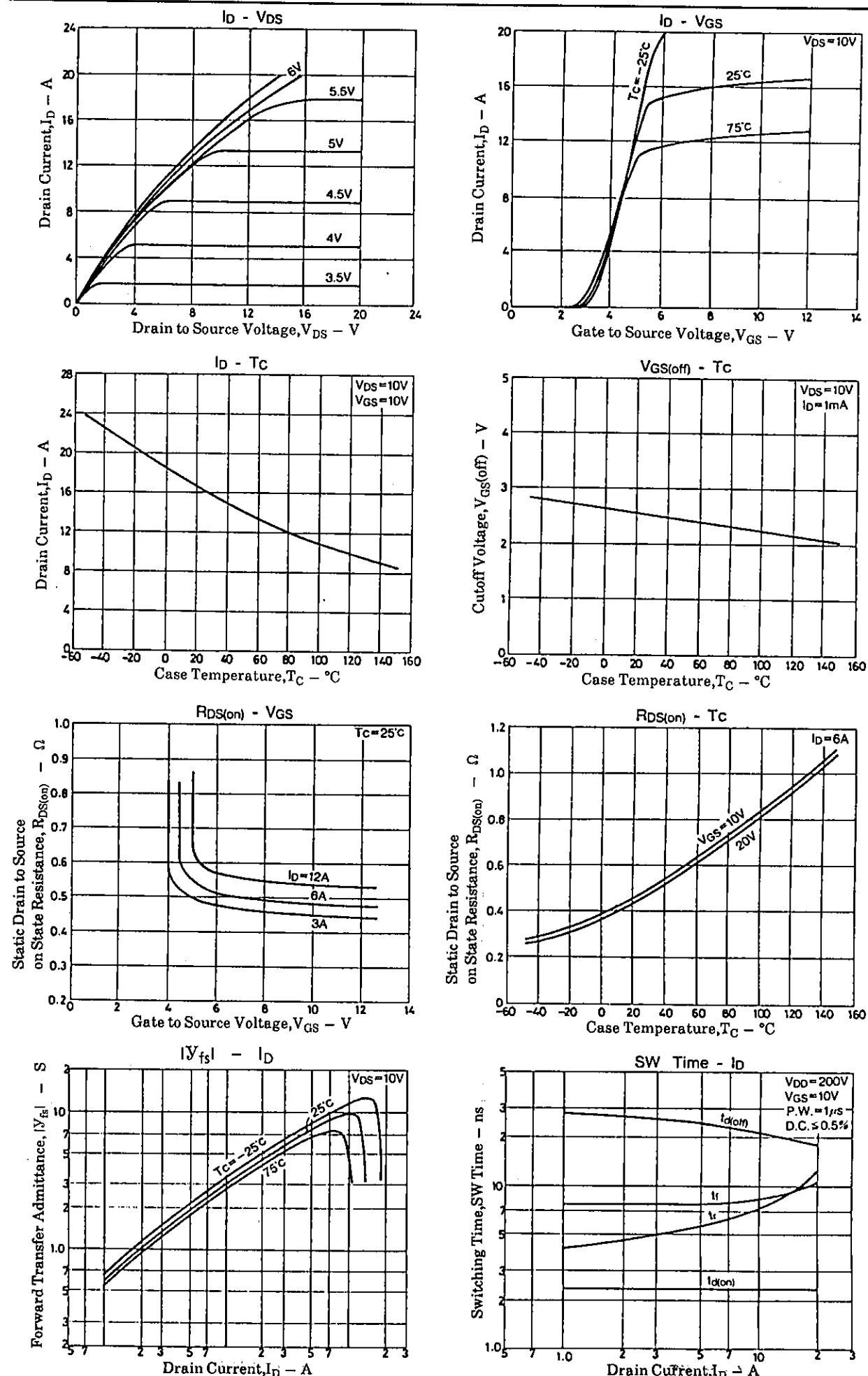
(Note) Be careful in handling the 2SK1452 because it has no protection diode between gate and source.

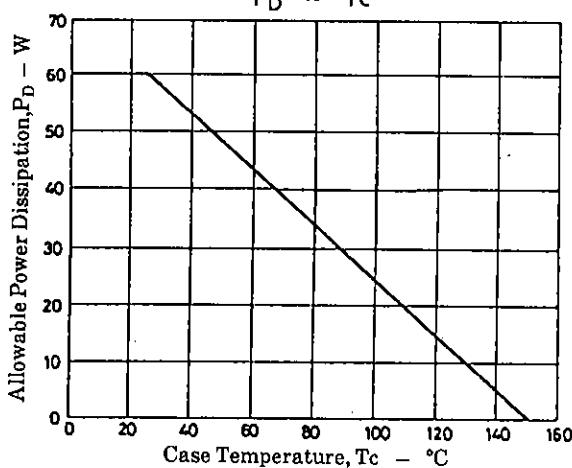
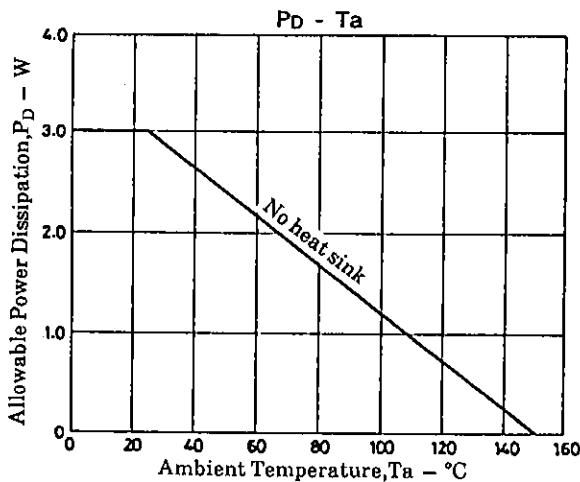
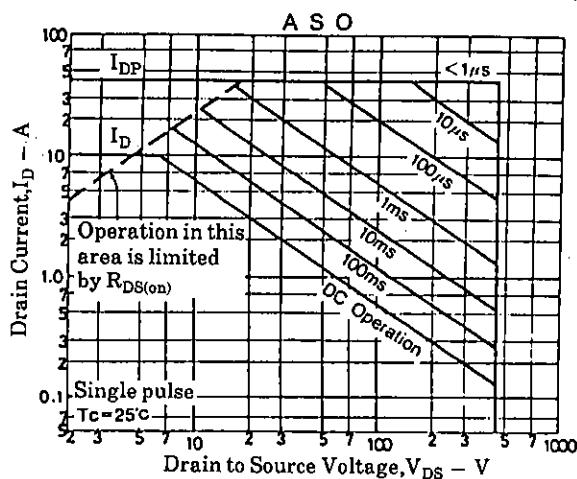
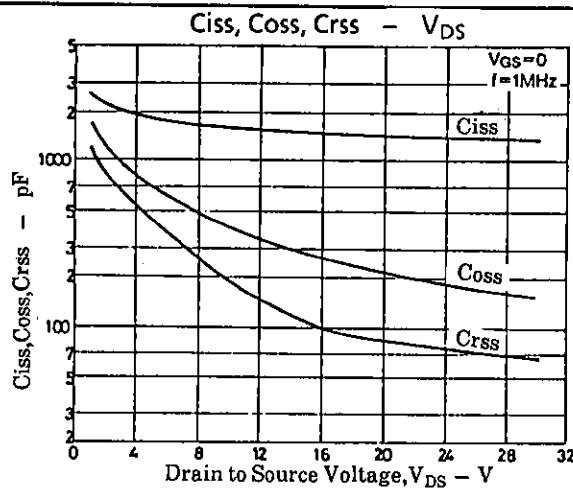
Switching Time Test Circuit**Package Dimensions 2076**

(unit : mm)

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